

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
1	IS&R	L1	14	(("4579752") or ("4671997") or ("4714632") or ("4173661") or ("5299731") or ("5480677") or ("6511760")).PN.	USP AT; US- PGP UB; EPO ; JPO ; DER WEN	2004/09 /29 17:29			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Err
1	BRS	L1	118 84	(428/446 or 428/450 or 428/451 or 428/452 or 428/454 or 428/926 or 428/938 or 427/585 or 427/588 or 427/255.23 or 427/255.395 or 427/294 or 427/31	USP AT; US- PGP UB; EPO ; JPO ; DER WEN T.	2004/09 /29 17:43			0
2	BRS	L2	174 8	1 and (silane or silicon ADJ hydride)	USP AT; US- PGP UB; EPO ; JPO ; DER WEN T.	2004/09 /29 17:43			0
3	BRS	L3	23	2 and silicon ADJ (dust or debris or contaminent or contaminents or particles)	USP AT; US- PGP UB; EPO ; JPO ; DER WEN T.	2004/09 /29 17:44			0
4	BRS	L4	11	3 and (cycling or cycled or repeating or repeated)	USP AT; US- PGP UB; EPO ; JPO ; DER WEN	2004/09 /29 18:03			0

	U	1	Document ID	Issue Date	Pag es	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 200401755 79 A1	2004090 9	7	Method for chemical vapor deposition of silicon on to substrates for use in corrosive and vacuum environments	428/446	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 200401755 78 A1	2004090 9	6	Method for chemical vapor deposition of silicon on to substrates for use in corrosive and vacuum environments	428/446	428/450; 428/457
3	<input type="checkbox"/>	<input type="checkbox"/>	US 200302322 00 A1	2003121 8	32	Multilayered optical structures	428/446	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6517913 B1	2003021 1	47	Method and apparatus for reducing perfluorocompound gases from substrate processing equipment emissions	427/588	427/585; 427/587; 588/227
5	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6511760 B1	2003012 8	5	Method of passivating a gas vessel or component of a gas transfer system using a silicon overlay coating	428/641	148/279; 148/508; 206/.6; 428/212; 428/336; 428/446
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5798137 A	1998082 5	34	Method for silicon deposition	427/213	216/37; 216/79; 423/349; 427/248. 1; 427/255. 23; 427/255. 5; 427/307
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5045398 A	1991090 3	12	Silicon carbide product	428/446	428/408; 428/698

	U	1	Document ID	Issue Date	Pag es	Title	Current OR	Current XRef
8	<input type="checkbox"/>	<input type="checkbox"/>	US 4871587 A	19891003	12	Process for coating an object with silicon carbide	427/249.16	427/113; 427/228; 427/255. 393; 427/255. 395; 427/255. 4; 427/376. 2; 427/399
9	<input type="checkbox"/>	<input type="checkbox"/>	US 4844980 A	19890704	10	Silica or silicic acid particles whose surface located hydroxyl groups are at least partially replaced by organic groups	428/405	106/481; 106/482; 106/490; 427/220; 428/446; 428/447; 516/100; 516/117; 516/144
10	<input type="checkbox"/>	<input type="checkbox"/>	US 4732801 A	19880322	9	Graded oxide/nitride via structure and method of fabrication therefor	428/198	257/753; 257/E21. 295; 427/123; 427/255. 37; 427/255. 393; 427/419. 7; 428/209; 428/210; 428/428; 428/446; 428/450; 428/469; 428/627; 428/628; 428/629; 428/665; 428/698; 428/901; 438/624; 438/974
11	<input type="checkbox"/>	<input type="checkbox"/>	US 4717585 A	19880105	23	Process for forming deposited film	427/568	136/258; 257/E21. 101; 427/561; 427/574; 427/585